

SLAC-PUB-12248
December 2006
(ACCPHY/MATSCI)

Enhancement of Spin-Polarized Electron Emission from Strain-Compensated AlInGaAs-GaAsP Superlattices *

J.S. Roberts

*Department of Electronic Engineering, University of Sheffield, Mappin St,
Sheffield, S1 3JD, UK*

Yu.P. Yashin, Yu. A. Mamaev, L.G. Gerchikov

State Polytechnic University, Politekhnikeskaya str., 29, 195251, St.-Petersburg, Russia

T. Maruyama, D.-A. Luh, J.E. Clendenin

Stanford Linear Accelerator Center, 2575 Sand Hill Road, Menlo Park, CA 94025, USA

Abstract

Resonance enhancement of the quantum efficiency of new polarized electron photocathodes based on a short-period strain-compensated AlInGaAs/GaAsP superlattice structure is reported. The superlattice is a part of an integrated Fabry-Perot optical cavity. We demonstrate that the Fabry-Perot resonator enhances the quantum efficiency by up to a factor 10 in the wavelength region of the main polarization maximum. The high structural quality implied by these results points to the very promising application of these photocathodes for spin-polarized electron sources.

Contributed to
The 17th International Spin Physics Symposium (SPIN 2006)
October 2-7, 2006, Kyoto, Japan

* Work supported in part by U.S. Department of Energy under contract DE-AC02-76SF00515.

Enhancement of Spin-Polarized Electron Emission from Strain-Compensated AlInGaAs-GaAsP Superlattices

J.S. Roberts

*Department of Electronic Engineering, University of Sheffield, Mappin St,
Sheffield, S1 3JD, UK*

Yu.P. Yashin, Yu. A. Mamaev, L.G.Gerchikov

State Polytechnic University, Politekhnicheskaya str., 29, 195251, St.-Petersburg, Russia

T. Maruyama, D.-A. Luh, J.E. Clendenin

Stanford Linear Accelerator Center, 2575 Sand Hill Road, Menlo Park, CA 94025, USA

Abstract. Resonance enhancement of the quantum efficiency of new polarized electron photocathodes based on a short-period strain-compensated AlInGaAs/GaAsP superlattice structure is reported. The superlattice is a part of an integrated Fabry-Perot optical cavity. We demonstrate that the Fabry-Perot resonator enhances the quantum efficiency by up to a factor 10 in the wavelength region of the main polarization maximum. The high structural quality implied by these results points to the very promising application of these photocathodes for spin-polarized electron sources.

Keywords: enhancement, quantum efficiency, Fabry-Perot resonator

PACS: 72.25.Fe, 73.21.Cd, 79.60.-i

INTRODUCTION

Strained short-period superlattices (SL) have been used to advantage in achieving highly spin-polarized electron photoemission [1]. In these structures, the heavy hole (hh) and light hole (lh) minibands are split due to the effects of both quantum confinement and strain-induced splitting. The enlarged valence band splitting results in a high initial electron polarization in the conduction band under excitation by circularly polarized light. Smearing of the interband absorption edge and light-heavy-hole mixture processes lead to a polarization (P) in the bandedge absorption of less than 100 %. The initial polarization can be increased by choosing strongly strained structures with a higher valence band splitting. The thickness of the strained photocathode working layer, however, exceeds the critical thickness for strain

relaxation resulting in structural defects, smaller residual strain and lower polarization. Critical thickness considerations limit the number of SL periods in the working layer and thus the quantum efficiency of the structures. To overcome this problem, two types of photocathodes have been proposed. The use of a strain compensated SL, whereby the composition of the SL barrier layers is chosen to have opposite (tensile) strain from that of the quantum well layers, allows the total working layer to be considerably thicker [2]. Another way to increase the quantum efficiency (QE) is to integrate the SL working layer into a Fabry-Perot optical cavity [3,4]. The key feature of such structures is a Distributed Bragg Reflector (DBR) at the back side of the photocathode that reflects the incoming circularly polarized light back to the surface where approximately 0.3 of the intensity is reflected into cathode again and so on.

In the present work we combine these two approaches and develop a novel photocathode structure that integrates a working layer based on the strain-compensated InAlGaAs-GaAsP SL into a Fabry-Perot optical cavity. We investigate polarized electron emission from the photocathodes with and without a DBR mirror and report a tenfold enhancement of quantum efficiency due to optical enhancement from the Fabry-Perot cavity without degradation of electron polarization.

Results and Discussion

The photocathode structures were grown on a p-type (100) GaAs substrate by Metal Organic Vapor Phase Epitaxy using trimethyl group III reagents and arsine. The photocathode consists of a DBR mirror containing 22 pairs of alternating $\lambda/4$ plates of $\text{Al}_{0.19}\text{Ga}_{0.81}\text{As}$ and AlAs. On the top of this mirror, a 500nm thick $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ buffer layer is grown that serves as the substrate for the strained SL. The superlattice contains 20 pairs of compressively-strained $(\text{Al}_{0.16}\text{Ga}_{0.84})_{0.82}\text{In}_{0.18}\text{As}$ quantum well layers and tensile-strained $\text{GaAs}_{0.83}\text{P}_{0.17}$ barrier layers. The layer compositions were designed to optimize the effect of strain magnitude and compensation on electron polarization. On top of the SL working layer, a 6-nm thick GaAs surface layer was deposited with Zn-doping concentration enlarged from $7 \times 10^{17} \text{ cm}^{-3}$ in the working layer to $1 \times 10^{19} \text{ cm}^{-3}$ to achieve negative electron affinity by the well known procedure of surface activation. Two samples have been prepared with and without a DBR layer.

The excitation spectra of the polarized photoemission from these structures were measured at room temperature for different activation regimes. Studies of polarization growth during assisted degradation were used to identify polarization losses in the band bending region (BBR).

The polarization and quantum efficiency data as a function of wavelength are shown in Fig. 1. The polarization spectra with and without the DBR layer are almost identical. The structures show all the typical features of SL emission including high-polarization peak at the band edge absorption and a second peak at higher energies with a well-pronounced dip between them. However these samples have different quantum yield spectra. While the sample without a DBR exhibits a typical smooth

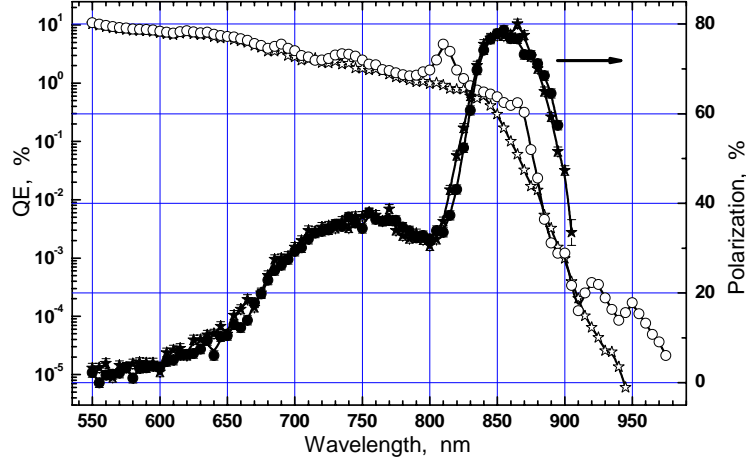


FIGURE 1. Polarization (solid symbols) and quantum efficiency (open symbols) spectra of the emitted photoelectrons from photocathodes with (circles) and without (stars) DBR

$QE(\lambda)$ behavior with a cutoff below the absorption edge, the quantum yield spectrum of the sample with a DBR has additional resonance features.

To illustrate this fact, we plot in Fig. 2 the ratio of quantum efficiencies for these two samples together with the polarization curve for the DBR sample. Resonance peaks correspond to the increase of the electromagnetic field in the working layer when resonance conditions for the Fabry-Perot optical cavity are fulfilled. The largest resonance peak of quantum yield enhancement at $\lambda=870\text{nm}$ practically coincides with the main polarization maximum of electron emission. Thus the DBR layer in the present sample increases the quantum efficiency of polarized electron emission by factor 10.

It worth to noting that the resonance enhancement of quantum yield is not accompanied by a decrease of electron polarization. This fact manifests the high structural quality of this photocathode. Since the resonance standing wave in a Fabry-Perot cavity is very sensitive to a phase shift near the resonance, even a small difference in the refraction indexes in in-plane directions as the result of a small anisotropy of the inplane lattice strain leads to a completely unpolarized wave in the working layer [4].

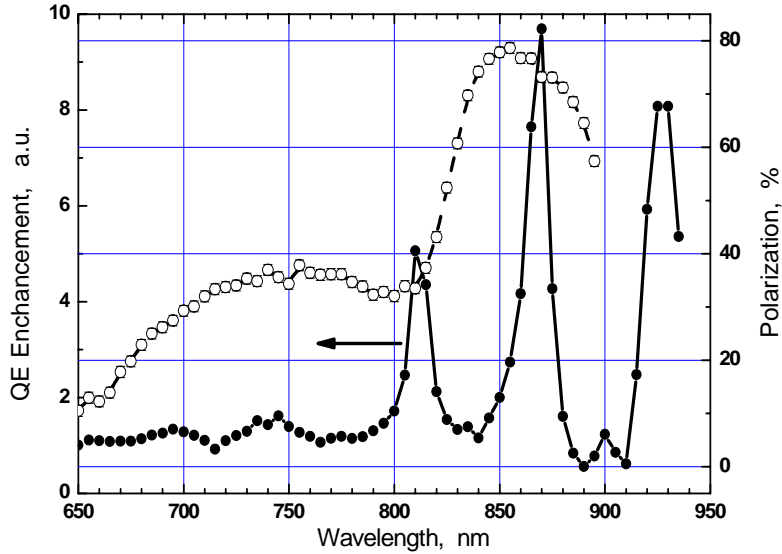


Figure 2. Resonance enhancement of quantum efficiency (solid circles) and polarization of electron emission (open circles) from photocathode with DBR.

To conclude, we have developed a novel type photocathode based on InAlGaAs-GaAsP strain compensated superlattices integrated into a Fabry-Perot optical cavity of high structural quality. We demonstrate a tenfold enhancement of quantum efficiency at the polarization maximum due to the multiple resonance reflection from DBR layer.

ACKNOWLEDGMENTS

This work was supported by RFBR under grant 04-02-16038, NATO under grant PST.CLG.979966, the U.S. Department of Energy under contract DE—AC02-76SF00515 and Swiss National Science Foundation under grant SNSF IB7420-111116

REFERENCES

1. A.V. Subashiev, Yu.A. Mamaev, Yu.P. Yashin, J.E. Clendenin, *Phys. Low-Dimensional Structures*, **1/2**, 1 (1999).
2. A. V. Subashiev, L. G. Gerchikov, Yu. A. Mamaev, Yu. P. Yashin, J. S. Roberts, D.-A. Luh, T. Maruyama, and J. E. Clendenin, *Appl. Phys. Lett.* **86**, 171911 (2005).
3. T. Saka, T.Kato, T.Nakanishi, M.Tsubata, K.Kishino, H.Horinaka, Y.Kamiya, S.Okumi, C.Takahashi, Y.Tanimoto, M.Tawada, K.Togawa, H.Aoyagi, S.Nakamura, *Jpn. J. Appl. Phys.* **32**, L1837 (1993).
4. J. C. Groebli, D. Oberli, F. Meier, A. Dommann, Yu. Mamaev, A. Subashiev and Yu. Yashin, *Phys. Rev. Lett.* **74**, 2106 (1995).